# Article information:

Intrinsic Semiconductor Technologies Secures £7m Investment to Solve the Memory Bottleneck for Data Hungry Applications
<https://www.design-reuse.com/news/53651/intrinsic-semiconductor-rram-funding.html>

# Article summary:

1. Intrinsic Semiconductor Technologies has secured £7 million in funding to bring its innovative approach to non-volatile memory using resistive random-access memory (RRAM) to market.

2. The technology can read data 10x to 100x faster and write it 1000x faster than existing solutions, allowing data hungry applications to overcome the memory bottleneck caused by current external flash memory.

3. Intrinsic sees many opportunities to integrate its technology with applications and devices that operate autonomously or remotely, ranging from driverless vehicles, robots in manufacturing, farming and warehouses to consumer applications around the home.

# Article rating:

Appears moderately imbalanced: The article provides some useful information, but is missing several important points or pieces of evidence that would be required to present the discussed topics in a balanced and reliable way. You are encouraged to seek a more balanced perspective on the presented issues by exploring the provided research topics and looking at different information sources.

# Article analysis:

The article discusses the £7 million investment secured by Intrinsic Semiconductor Technologies to develop its innovative approach to non-volatile memory using resistive random-access memory (RRAM). The technology can read data 10x to 100x faster and write it 1000x faster than existing solutions, making it a potential solution for data-hungry applications that require higher performance at lower energy consumption. The article highlights the potential of RRAM to become the backbone for the next generation of edge and IoT computers, enabling companies to integrate more intelligence into self-contained applications and devices so that they can operate autonomously.

The article is well-written and informative, providing details about Intrinsic's technology and its potential applications. However, there are some biases in the article that need to be addressed. Firstly, the article presents only one side of the story, highlighting the benefits of Intrinsic's technology without exploring any potential drawbacks or limitations. While RRAM has many advantages over existing solutions, it is important to note any possible risks or challenges associated with its implementation.

Secondly, the article is promotional in nature, focusing on Intrinsic's achievements and future prospects rather than providing a balanced analysis of its technology. While it is understandable that the company wants to promote its product, it would have been helpful if the article had provided more information about how RRAM compares with other emerging technologies in this space.

Thirdly, there are some unsupported claims in the article that need further evidence. For example, while Yole Intelligence estimates that embedded RRAM market will grow from $18m in 2021 to $957m in 2027 at a 94% CAGR, there is no explanation as to how this estimate was arrived at or what factors were considered.

Overall, while the article provides useful information about Intrinsic's technology and its potential applications, it could have been more balanced and less promotional in nature. It would have been helpful if the article had explored potential drawbacks or limitations of RRAM and provided more evidence to support its claims.

# Topics for further research:

* Limitations of resistive random-access memory (RRAM) technology
* Comparison of RRAM with other emerging memory technologies
* Challenges associated with implementing RRAM in edge and IoT devices
* Potential risks of using RRAM for non-volatile memory
* Factors influencing the growth of embedded RRAM market
* Future developments in non-volatile memory technology beyond RRAM

# Report location:

<https://www.fullpicture.app/item/2b6b155e1997381742670fee2a248ac0>